

# NAVOLCHI 3<sup>rd</sup> Review Meeting

November 5<sup>th</sup> 2014, Brussels



FP7-ICT-2011-7  
GA 288869

**Work Package 6: Integration, Characterization & Testing**

**“Project NAVOLCHI“**

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**ETH Zurich, Switzerland**



**Nano Scale Disruptive Silicon-Plasmonic Platform  
for Chip-to-Chip Interconnection**

[www.navolchi.eu](http://www.navolchi.eu)

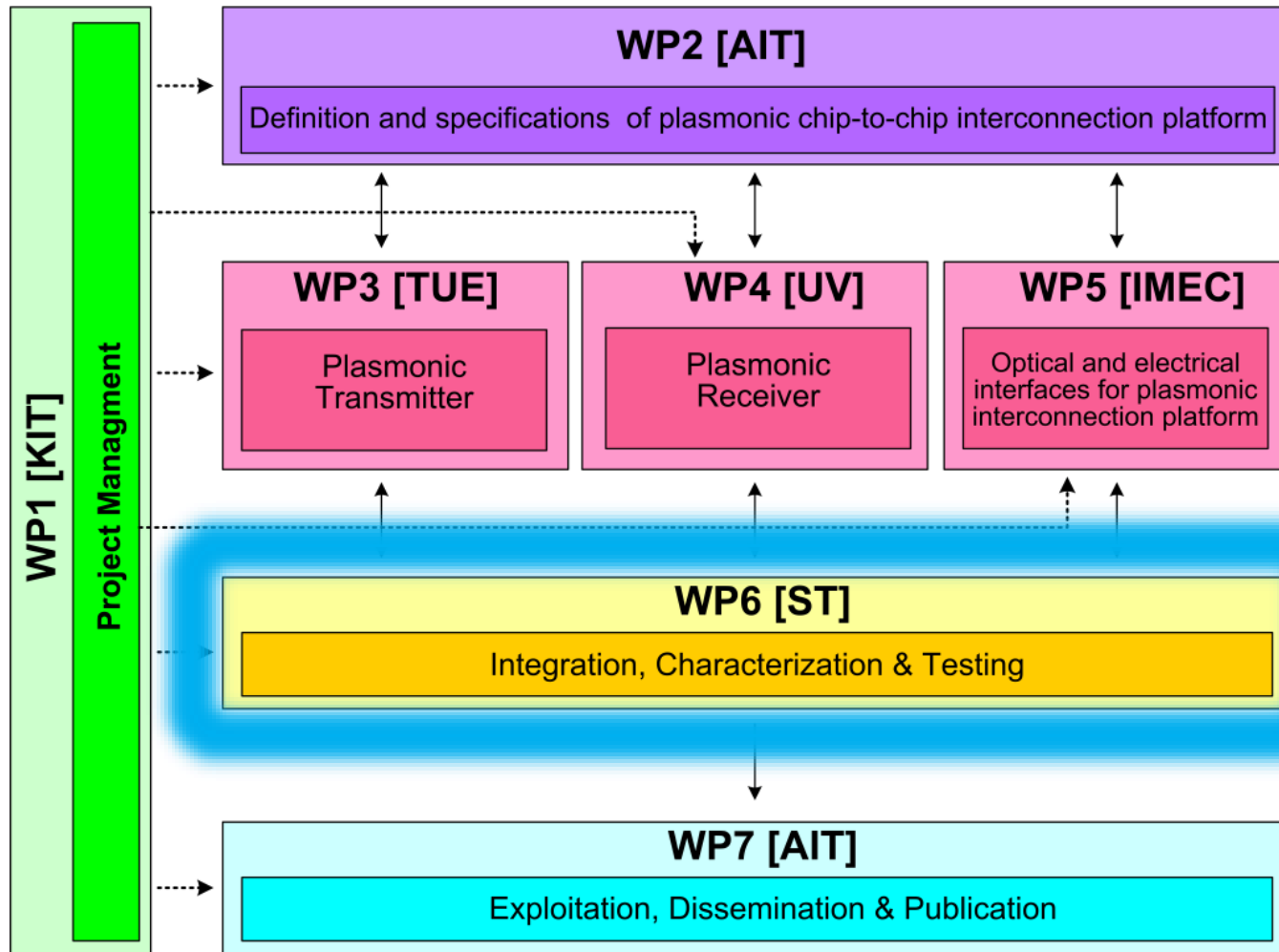
# Outline

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- 1. WP6 Position in Project**
- 2. Objectives**
- 3. Tasks**
- 4. Milestones and Deliverables**
- 5. Status of Work**
  - Task 6.1 Characterization of active and passive plasmonic devices**
  - Task 6.2 Assembly and packaging of plasmonic devices into System in Package Interconnect System – Contingency Plan**
- 6. Summary and Outlook**

# WP6 Position in Project



## Contributors:



# Objectives

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- Characterization and **testing of** active and passive **plasmonic devices**
- **Integration** of plasmonic devices **with the electrical parts** the chip-to-chip communication structure is composed of
- Characterization and **testing of a complete System in Package**

# Tasks

	<b>Names of the Tasks</b>	<b>Time Period [months]</b>
Task 6.1	Characterization of active and passive plasmonic devices	7 – 33
Task 6.2	Assembly and packaging of plasmonic devices into System in Package	30 – 36
Task 6.3	Plasmonic chip to chip interconnect prototype testing and evaluation	32 – 36 → 45
Task 6.4	System-in-Package integration and characterization	22 – 36 → 45

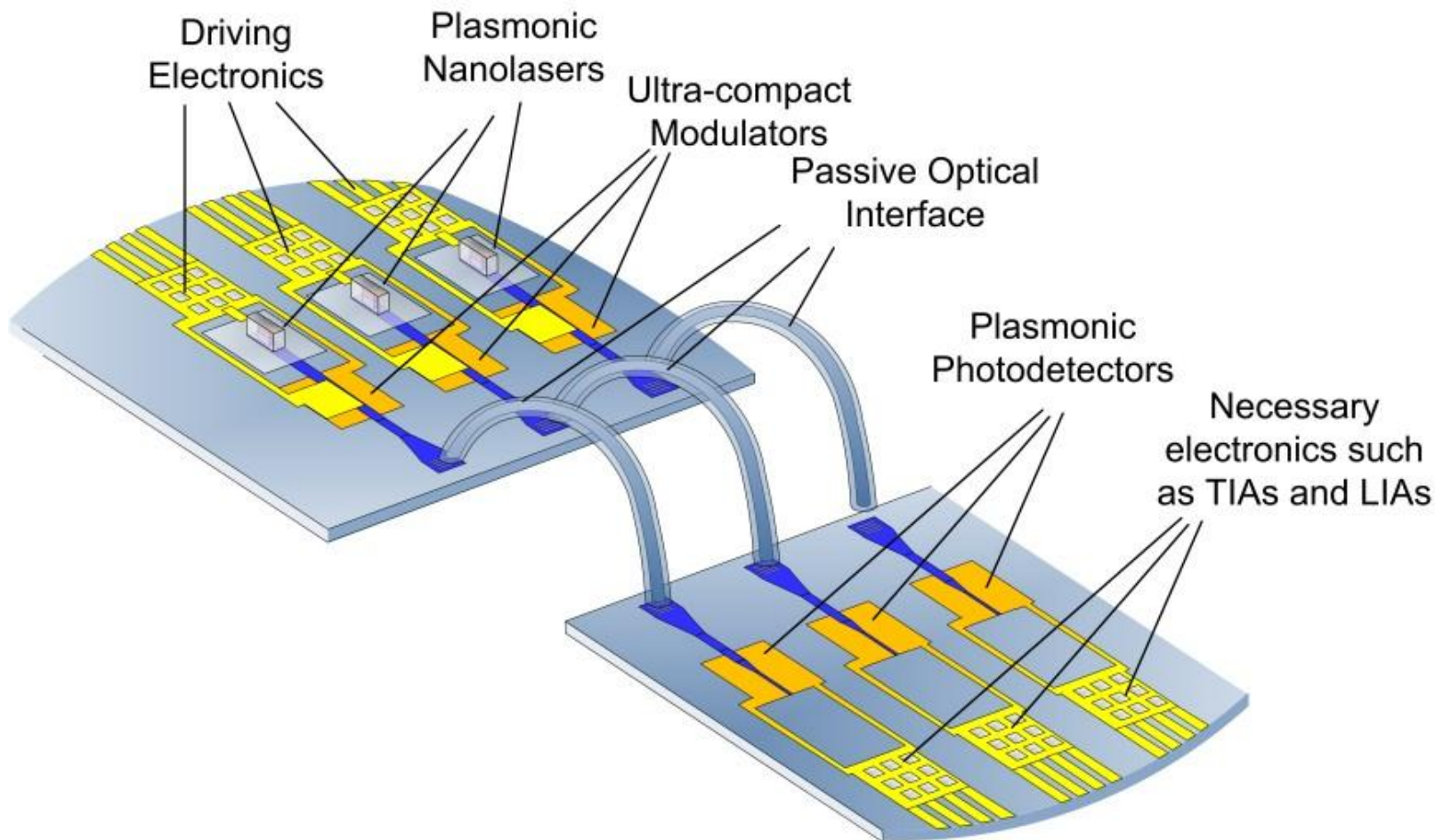
# Milestones

	<b>Names of the Milestones</b>	<b>Month</b>	<b>Partner</b>
MS37	Plasmonic active device characterization results	12	KIT
MS38	Plasmonic passive components characterization results with a 1dB coupling loss	24	KIT
MS39	Concept for system integration developed	27	AIT
MS40	Individual plasmonic devices characteriaztion, testing and evaluation	30 → 39	TU/e
MS41	Chip to chip interconnect characterization	33 → 42	ST
MS42	Plasmonic components integration to demonstrate chip-to-chip interconnect	33 → 42	AIT
MS43	Plasmonic chip to chip interconnect prototype testing and evaluation	36 → 45	ST

# Deliverables

	<b>Names of the Deliverables</b>	<b>Month</b>	<b>Partner</b>
D6.1	Report on characterization results of all plasmonic devices	(27) 36	TU/e
D6.2	Report on characterization results of all optical interface plasmonic passive components	(27) 36	KIT
D6.3	Report on chip to chip interconnect characterization	36 → 45	ETH
D6.4	Report on plasmonic chip-to-chip interconnect prototype testing and evaluation	36 → 45	AIT

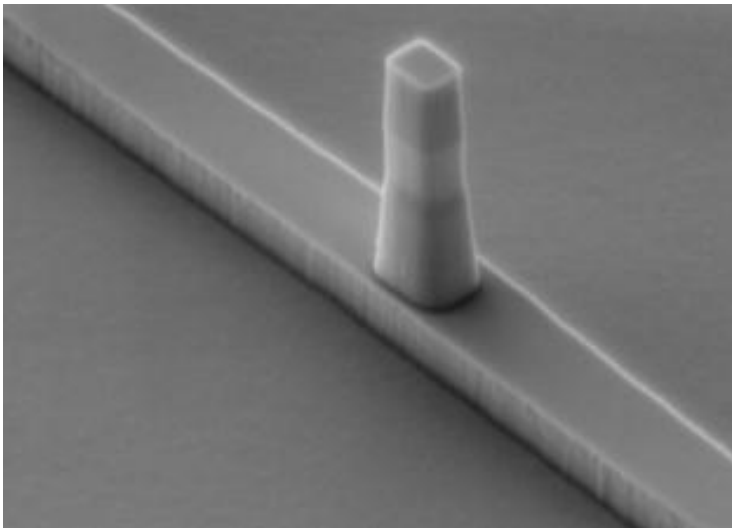
# WP6: Assembly to Plasmonic Chip-to-Chip Interconnect Array





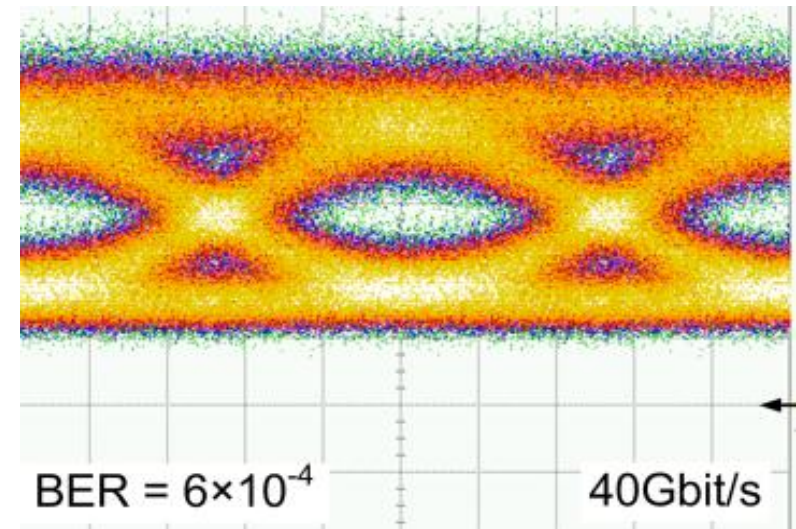
# Task 6.1 Characterization of Active and Passive Plasmonic Devices

## Laser



- Fabrication process of III-V laser on silicon fully developed
- Characterization beginning of next year

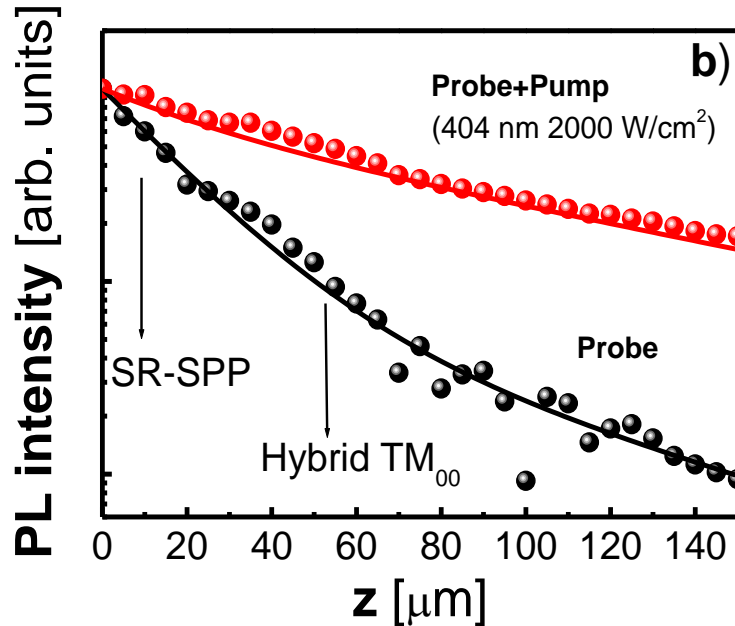
## Mach-Zehnder Modulator



- Data rates: 40 Gbit/s (BER  $6 \times 10^{-4}$ )
- Energy consumption: 75...225 fJ/bit
- Device length: 29  $\mu\text{m}$
- Loss: 12 dB

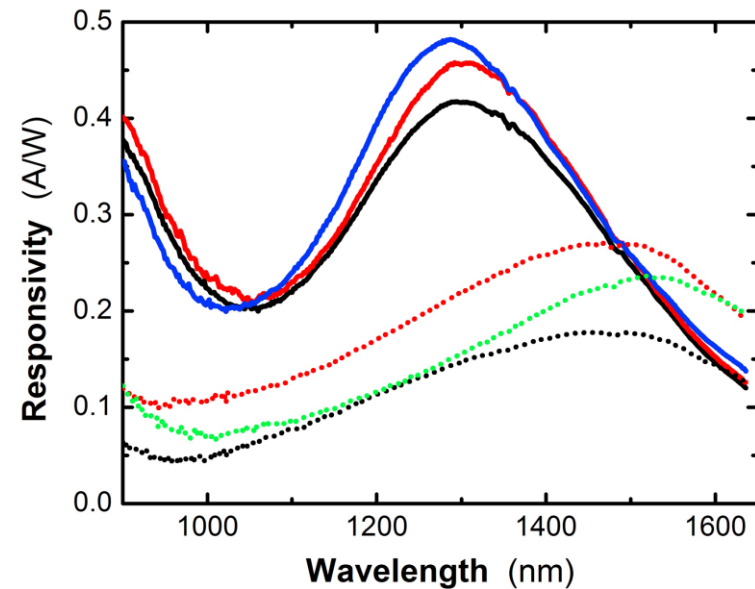
# Task 6.1 Characterization of Active and Passive Plasmonic Devices

## Amplifier



- @1550 nm: compensation of losses, no gain yet
- Outlook: gain by using HgTe QDs in dielectric matrix

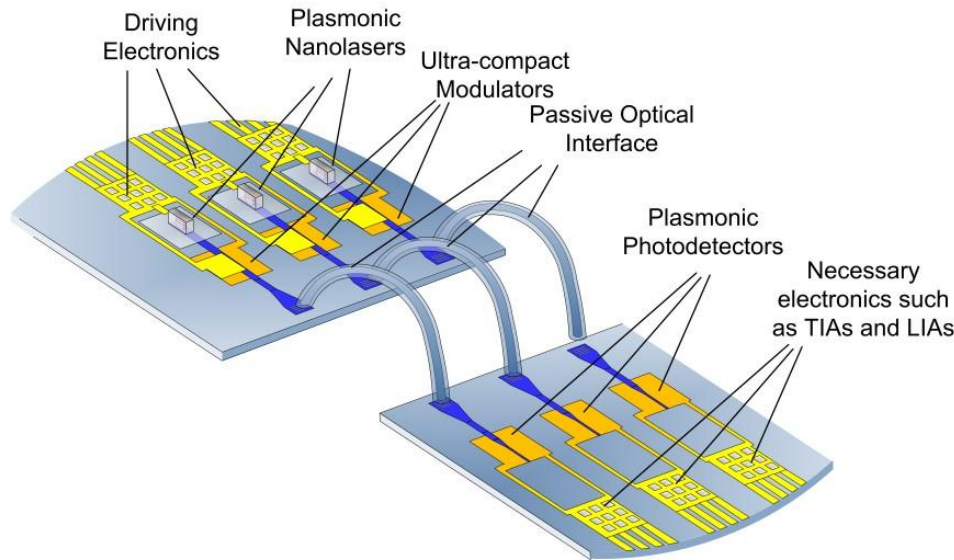
## Photodetector



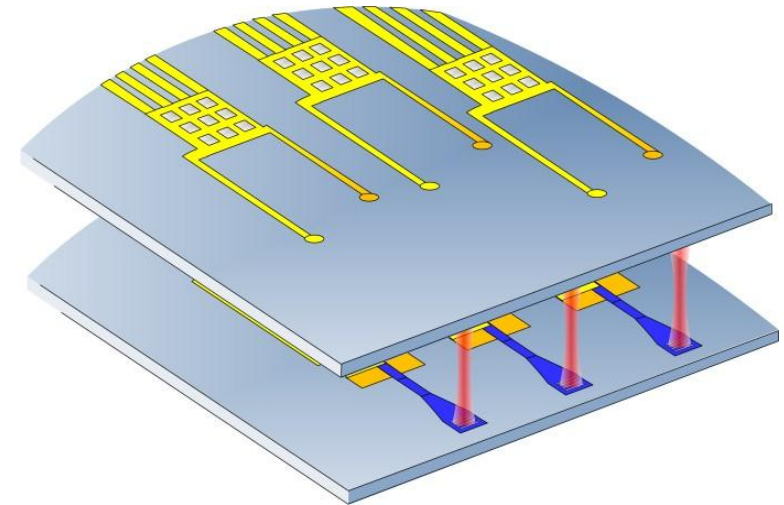
- Schottky:
  - Responsivity: 0.1-0.3 A/W
  - Speed limited
- Outlook: Nano-gap PDs

# Task 6.2 Assembly and Packaging of Plasmonic Devices into System in Package

## 2D in-plane packaging

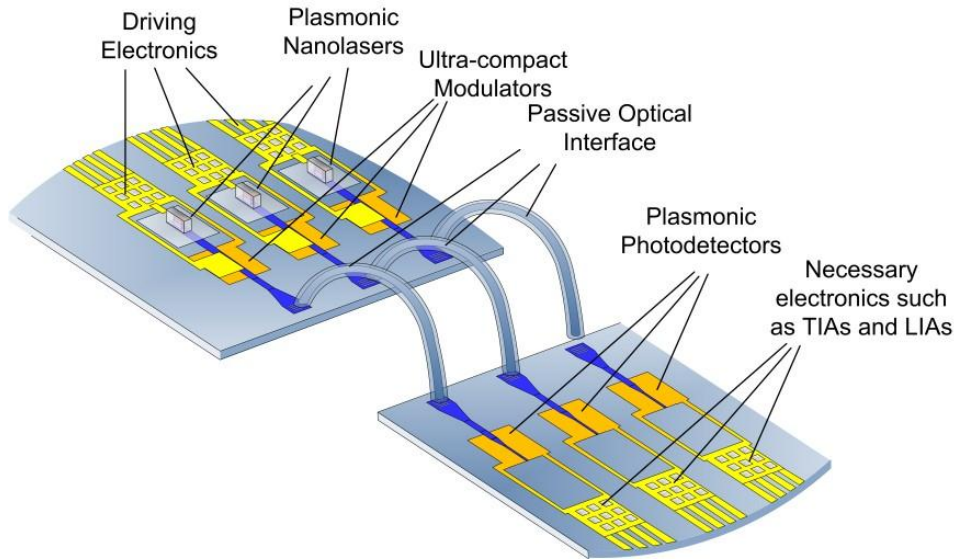


## 3D vertical stacking

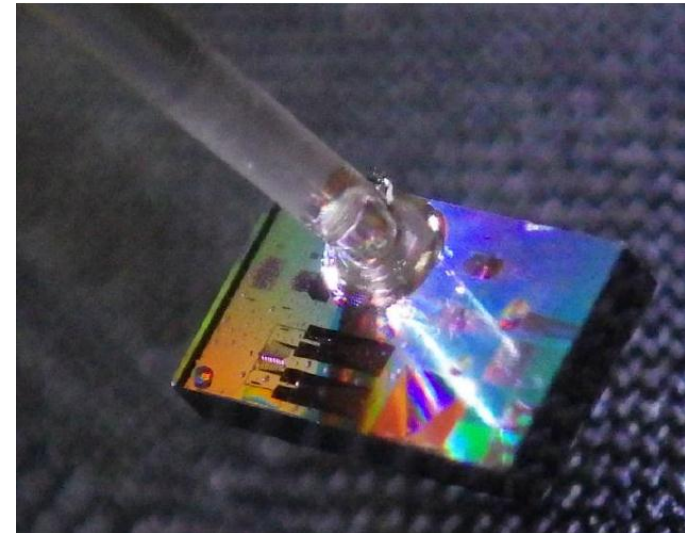


# Task 6.2 Assembly and Packaging of Plasmonic Devices into System in Package

## 2D in-plane packaging



## Commercial fiber arrays (Chiral Photonics)



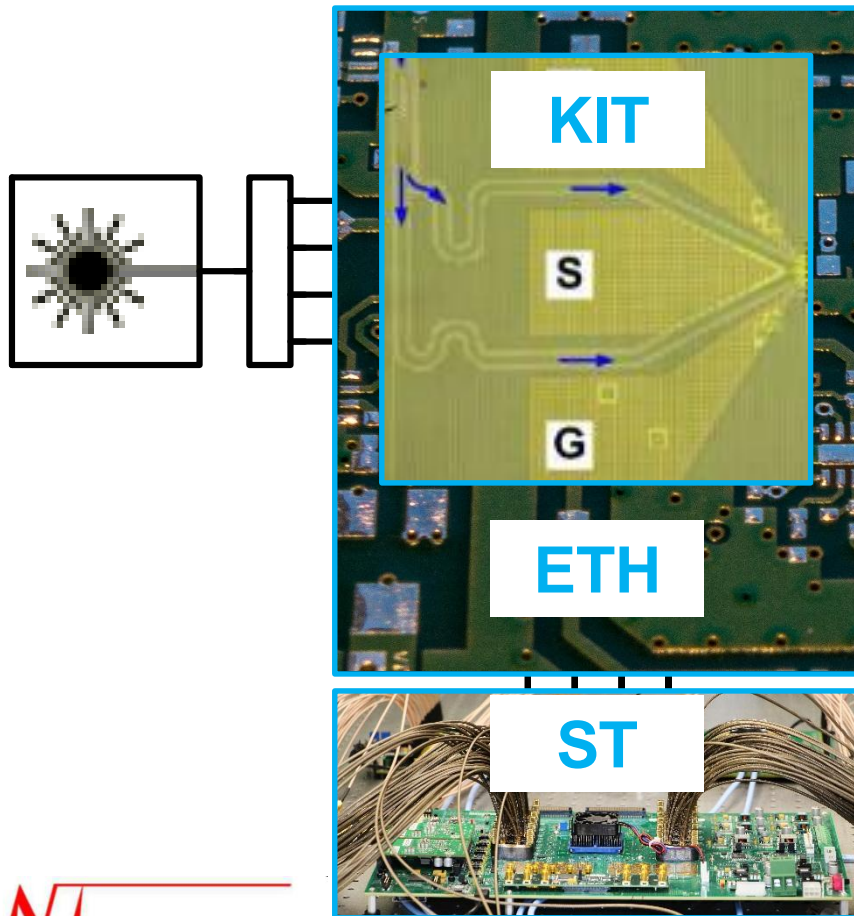
[1]

## Advantages

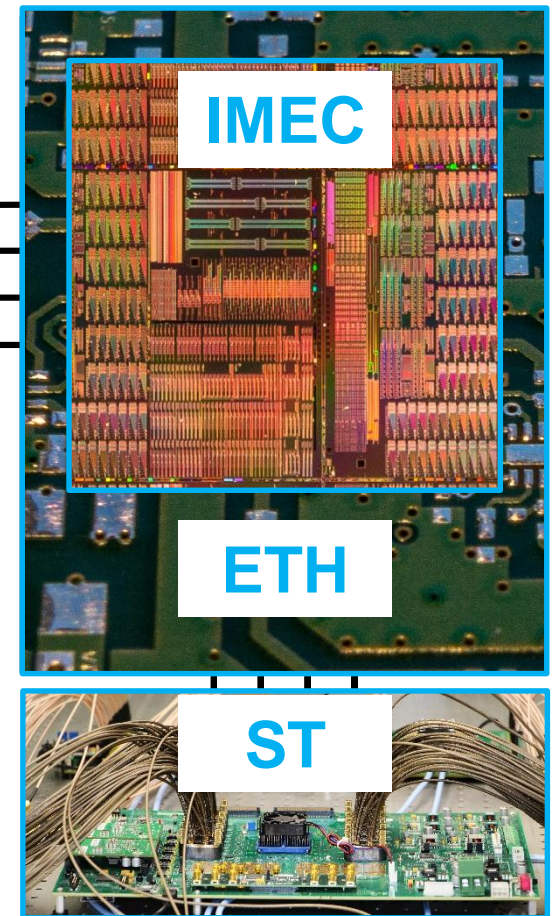
- 4 channels with 50  $\mu\text{m}$  pitch
- Interchannel coupling  $< -35$  dB
- No additional fabrication steps
- Allows for additional optical amplifier

# Interconnect System – Contingency Plan

## Transmitter



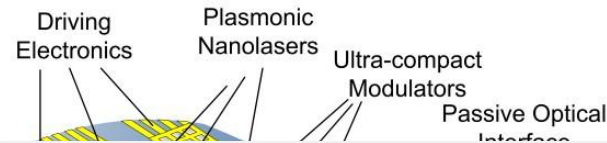
## Receiver



# Interconnect System – Contingency Plan

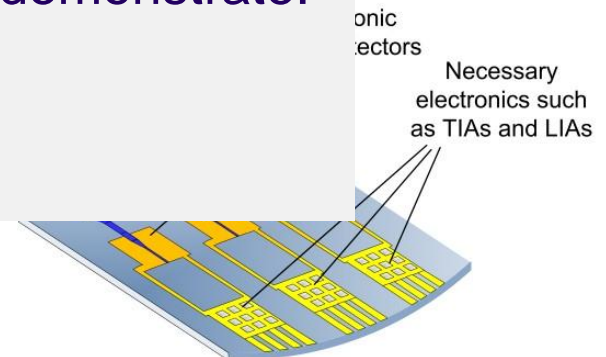
## System Level Specifications Transmitter

- 4 optical channels with 50  $\mu\text{m}$  pitch (modulator length: 29  $\mu\text{m}$ )
- Data rate: 40 Gbit/s
- Optical bandwidth: 120 nm
- Energy consumption modulator: 75 fJ/bit
- Insertion loss: 12 dB



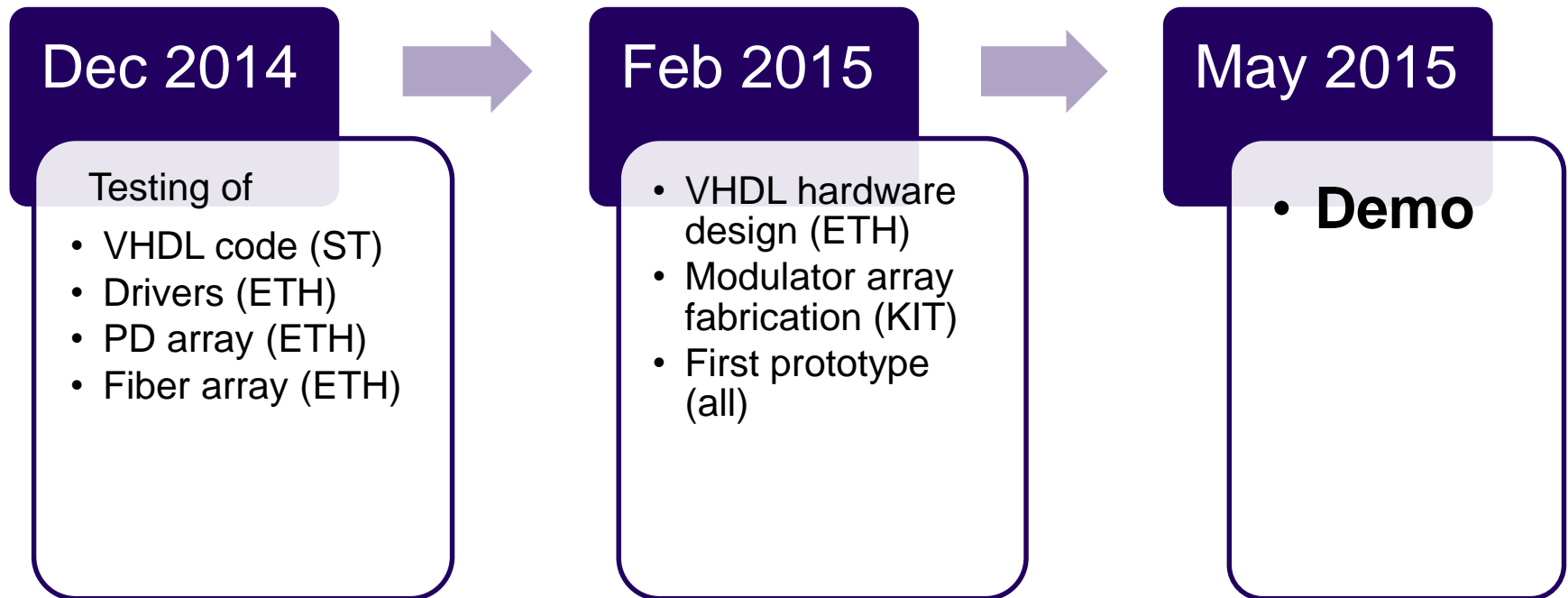
NAVOLCHI interconnect system will demonstrate:

- Small footprint
- High speed
- Broadband operation



# Interconnect System – Contingency Plan

## Timeline



# Summary and Outlook

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- **Summary**
  - Progress in characterization of active and passive plasmonic devices
  - Integration of plasmonic devices with the electrical parts started
- **Outlook**
  - Complete integration of plasmonic devices with the electrical parts
  - Characterization and testing of a complete System in Package